5-V/3.3-V SINGLE-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER

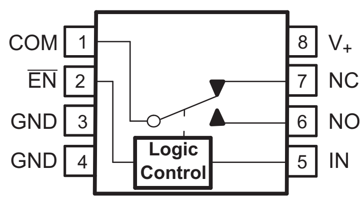
FEATURES

- **Isolation in the Powered-Off Mode, $V_+ = 0$**
- **Specified Break-Before-Make Switching**
- **Low ON-State Resistance (1 Ω)**
- **Control Inputs Are 5.5-V Tolerant**
- **Low Charge Injection**
- **Excellent ON-State Resistance Matching**
- **Low Total Harmonic Distortion (THD)**
- **1.65-V to 5.5-V Single-Supply Operation**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2000-V Human-Body Model (A114-B, Class II)**
  - **1000-V Charged-Device Model (C101)**

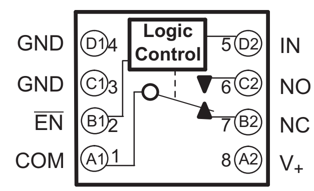
APPLICATIONS

- **Cell Phones**
- **PDAs**
- **Portable Instrumentation**
- **Audio and Video Signal Routing**
- **Low-Voltage Data-Acquisition Systems**
- **Communication Circuits**
- **Modems**
- **Hard Drives**
- **Computer Peripherals**
- **Wireless Terminals and Peripherals**

DCU PACKAGE (TOP VIEW)



YZP PACKAGE (BOTTOM VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS5A3153 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance and an excellent on-resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has an excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

ORDERING INFORMATION

T_A	PACKAGE(1)(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING(3)
–40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	TS5A3153YZPR	_ _ _J57
	SSOP – DCU	Reel of 3000	TS5A3153DCUR	JCD_

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
(3) DCU: The actual top-side marking has one additional character that designates the assembly/test site.
YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

FUNCTION TABLE

$\overline{EN}$	IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	L	ON	OFF
L	H	OFF	ON
H	X	OFF	OFF

Summary of Characteristics(1)

Configuration	Single-Pole, Double-Throw 2:1 Multiplexer/Demultiplexer (SPDT)
Number of channels	1
ON-state resistance (r_{on})	1.1 Ω
ON-state resistance match (Δr_{on})	0.1 Ω
ON-state resistance flatness ($r_{on(flat)}$)	0.15 Ω
Turn-on/turn-off time (t_{ON}/t_{OFF})	20 ns/15 ns
Make-before-break time (t_{MBB})	12 ns
Charge injection (Q_C)	36 pC
Bandwidth (BW)	100 MHz
OFF isolation (O_{ISO})	–65 dB at 1 MHz
Crosstalk (X_{TALK})	–68 dB at 1 MHz
Total harmonic distortion (THD)	0.01%
Leakage current ($I_{COM(OFF)}$/$I_{NC(OFF)}$)	±20 nA
Power-supply current (I_+)	0.1 µA
Package option	8-pin SSOP or DSBGA

(1) $V_+ = 5$ V, $T_A = 25°C$

ABSOLUTE MINIMUM AND MAXIMUM RATINGS[(1)(2)]

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_+	Supply voltage range[(3)]		–0.5	6.5	V
V_{NC}, V_{NO}, V_{COM}	Analog voltage range[(3)(4)(5)]		–0.5	V_+ + 0.5	V
I_K	Analog port diode current	V_{NC}, V_{NO}, V_{COM} < 0 or V_{NO}, V_{NC}, V_{COM} > V_+	–50		mA
I_{NC}, I_{COM}, I_{NO}	On-state switch current	V_{NC}, V_{NO}, V_{COM} = 0 to V_+	–200	200	mA
	On-state peak switch current[(6)]		–400	400	
V_I	Digital input voltage range[(3)(4)]		–0.5	6.5	V
I_{IK}	Digital input clamp current	V_I < 0	–50		mA
I_+	Continuous current through V_+			100	mA
I_{GND}	Continuous current through GND		–100	100	mA
θ_{JA}	Package thermal impedance[(7)]	DCU package		227	°C/W
		YZP package		102	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) Pulse at 1-ms duration < 10% duty cycle.
(7) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY(1)

V_+ = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	V
Peak ON resistance	r_{peak}	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	4.5 V		0.9	1.1	Ω
				Full				1.3	
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	4.5 V		0.8	0.9	Ω
				Full				1.1	
ON-state resistance matching between channels	Δr_{on}	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	4.5 V		0.05	0.1	Ω
				Full				0.1	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	4.5 V		0.15		Ω
				Full					
		V_{NO} or V_{NC} = 1 V, 1.5 V, 2.5 V, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C			0.09	0.15	
				Full				0.15	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = 4.5 V, or V_{NC} or V_{NO} = 4.5 V, V_{COM} = 1 V,	Switch OFF, See Figure 14	25°C	5.5 V	–20	2	20	nA
				Full		–150		150	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 5.5 V, V_{COM} = 5.5 V to 0,	Switch OFF, See Figure 14	25°C	0 V	–5	0.7	5	µA
				Full		–25		25	
NC, NO ON leakage current	$I_{NC(ON)}$, $I_{NO(ON)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = Open, or V_{NC} or V_{NO} = 4.5 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	5.5 V	–20	2	20	nA
				Full		–150		150	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NC} or V_{NO} = 4.5 V, or V_{COM} = 4.5 V, V_{NC} or V_{NO} = 1 V,	Switch OFF, See Figure 14	25°C	5.5 V	–20	2	20	nA
				Full		–150		150	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 0 to 5.5 V, V_{COM} = 5.5 V to 0,	Switch OFF, See Figure 14	25°C	0 V	–5	0.7	5	µA
				Full		–25		25	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NC} or V_{NO} = Open, or V_{COM} = 4.5 V, V_{NC} or V_{NO} = Open,	Switch ON, See Figure 15	25°C	5.5 V	–20	2	20	nA
				Full		–150		150	
Digital Control Inputs (IN, $\overline{EN}$)(2)									
Input logic high	V_{IH}			Full		2.4		5.5	V
Input logic low	V_{IL}			Full		0		0.8	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0 V		25°C	5.5 V	–100	25	100	nA
				Full		–100		100	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (continued)

V_+ = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	1	12.5	16	ns
				Full	4.5 V to 5.5 V	1		17.5	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	2.5	8.5	15	ns
				Full	4.5 V to 5.5 V	2		18	
Break-before-make time	t_{MBB}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	5 V	1	7	12	ns
				Full	4.5 V to 5.5 V	0.5		15	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 22	25°C	5 V		12		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or V_{NO} = V_+ or GND,	Switch OFF, See Figure 16	25°C	5 V		19		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND,	Switch ON, See Figure 16	25°C	5 V		57		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND,	Switch ON, See Figure 16	25°C	5 V		36		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND,	Switch ON, See Figure 16	25°C	5 V		57		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	5 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 19	25°C	5 V		97		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 20	25°C	5 V		–64		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	Switch ON, See Figure 21	25°C	5 V		–64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 23	25°C	5 V		0.004		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	5.5 V		0.02	0.1	µA
				Full				0.5	

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY(1)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	V
Peak ON resistance	r_{peak}	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	3 V		1.3	1.6	Ω
				Full				1.8	
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 2 V, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	3 V		1.2	1.5	Ω
				Full				1.7	
ON-state resistance match between channels	Δr_{on}	V_{NO} or V_{NC} = 2 V, 0.8 V I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	3 V		0.08	0.15	Ω
				Full				0.15	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C	3 V		0.2		Ω
				Full					
		V_{NO} or V_{NC} = 2 V, 0.8 V, I_{COM} = –100 mA,	Switch ON, See Figure 13	25°C			0.09	0.15	
				Full				0.15	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = 3 V, or V_{NC} or V_{NO} = 3 V, V_{COM} = 1 V,	Switch OFF, See Figure 14	25°C	3.6 V	–20	2	20	nA
				Full		–50		50	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 3.6 V, V_{COM} = 3.6 V to 0 V,	Switch OFF, See Figure 14	25°C	0 V	–1	0.2	1	µA
				Full		–15		15	
NC, NO ON leakage current	$I_{NC(ON)}$, $I_{NO(ON)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = Open, or V_{NC} or V_{NO} = 3 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	3.6 V	–20	2	20	nA
				Full		–50		50	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NC} or V_{NO} = 3 V, or V_{COM} = 3 V, V_{NC} or V_{NO} = 1 V,	Switch OFF, See Figure 14	25°C	3.6 V	–20	2	20	nA
				Full		–50		50	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 0 to 3.6 V, V_{COM} = 3.6 V to 0,	Switch OFF, See Figure 14	25°C	0 V	–1	0.2	1	µA
				Full		–15		15	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NC} or V_{NO} = Open, or V_{COM} = 3 V, V_{NC} or V_{NO} = Open	Switch ON, See Figure 15	25°C	3.6 V	–20	2	20	nA
				Full		–50		50	
Digital Control Inputs (IN, $\overline{EN}$)(2)									
Input logic high	V_{IH}			Full		2		5.5	V
Input logic low	V_{IL}			Full		0		0.8	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	3.6 V	–100	25	100	nA
				Full		–100		100	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (continued)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	1	17	22	ns
				Full	3 V to 3.6 V	1		24	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	4.3	9.5	16	ns
				Full	3 V to 3.6 V	4		19	
Break-before-make time	t_{MBB}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	3.3 V	2	12	22	ns
				Full	3 V to 3.6 V	1		25	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 22	25°C	3.3 V		8		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch OFF, See Figure 16	25°C	3.3 V		19		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch ON, See Figure 16	25°C	3.3 V		57		pF
COM OFF capacitance	$C_{COM(OFF)}$	$V_{COM} = V_+$ or GND,	Switch ON, See	25°C	3.3 V		36		pF
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND,	Switch ON, See Figure 16	25°C	3.3 V		57		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND,	See Figure 16	25°C	3.3 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 19	25°C	3.3 V		97		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 20	25°C	3.3 V		–64		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	Switch ON, See Figure 21	25°C	3.3 V		–64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.01		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	3.6 V		0.01	0.1	µA
				Full				0.25	

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY(1)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V_{COM}, V_{NO}, V_{NC}				0		V_+	V
Peak ON resistance	r_{peak}	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –8 mA, Switch ON, See Figure 13	25°C	2.3 V		1.9	2.5	Ω
			Full				2.7	
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 1.8 V, I_{COM} = –8 mA, Switch ON, See Figure 13	25°C	2.3 V		1.6	2.1	Ω
			Full				2.5	
ON-state resistance matching between channels	Δr_{on}	V_{NO} or V_{NC} = 1.8 V, I_{COM} = –8 mA, Switch ON, See Figure 13	25°C	2.3 V		0.12	0.2	Ω
			Full				0.2	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –8 mA, Switch ON, See Figure 13	25°C	2.3 V		0.65		Ω
		V_{NO} or V_{NC} = 0.8 V, 1.8 V, I_{COM} = –8 mA, Switch ON, See Figure 13	25°C	2.3 V		0.5	1	Ω
			Full				1	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 0.5 V, V_{COM} = 2.2 V, or V_{NC} or V_{NO} = 2.2 V, V_{COM} = 0.5 V, Switch OFF, See Figure 14	25°C	2.7 V	–20	2	20	nA
			Full		–50		50	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 2.7 V, V_{COM} = 2.7 V to 0, Switch OFF, See Figure 14	25°C	0 V	–1	0.1	1	µA
			Full		–10		10	
NC, NO ON leakage current	$I_{NC(ON)}$, $I_{NO(ON)}$	V_{NC} or V_{NO} = 0.5 V, V_{COM} = Open, or V_{NC} or V_{NO} = 2.2 V, V_{COM} = Open, Switch ON, See Figure 15	25°C	2.7 V	–20		20	nA
			Full		–50		50	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 0.5 V, V_{NC} or V_{NO} = 2.2 V, or V_{COM} = 2.2 V, V_{NC} or V_{NO} = 0.5V, Switch OFF, See Figure 14	25°C	2.7 V	–20		20	nA
			Full		–50		50	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 0 to 2.7 V, V_{COM} = 2.7 V to 0, Switch OFF, See Figure 14	25°C	0 V	–1		1	µA
			Full		–10		10	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.5 V, V_{NC} or V_{NO} = Open, or V_{COM} = 2.2 V, V_{NC} or V_{NO} = Open, Switch ON, See Figure 15	25°C	2.7 V	–20		20	nA
			Full		–50		50	
Digital Control Inputs (IN, $\overline{EN}$)(2)								
Input logic high	V_{IH}		Full		1.8		5.5	V
Input logic low	V_{IL}		Full		0		0.6	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0	25°C	2.7 V	–100	25	100	nA
			Full		–100		100	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY (continued)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	1.7	24	31	ns
				Full	2.3 V to 2.7 V	1.5		33.5	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	5.2	10.5	17	ns
				Full	2.3 V to 2.7 V	5		20	
Break-before-make time	t_{MBB}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	2.5 V	3	10	30	ns
				Full	2.3 V to 2.7 V	2		40	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 22	25°C	2.5 V		6		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch OFF, See Figure 16	25°C	2.5 V		19		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch ON, See Figure 16	25°C	2.5 V		57		pF
COM OFF capacitance	$C_{COM(OFF)}$	$V_{COM} = V_+$ or GND,	Switch ON, See Figure 16	25°C	2.5 V		36		pF
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND,	Switch ON, See Figure 16	25°C	2.5 V		57		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND,	See Figure 16	25°C	2.5 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 19	25°C	2.5 V		100		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 20	25°C	2.5 V		–64		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	Switch ON, See Figure 21	25°C	2.5 V		–64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.020		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	2.7 V		0.001	0.05	µA
				Full				0.15	

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY(1)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	V
Peak ON resistance	r_{peak}	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –2 mA,	Switch ON, See Figure 13	25°C	1.65 V		5.2	15	Ω
				Full				20	
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 1.5 V, I_{COM} = –2 mA,	Switch ON, See Figure 13	25°C	1.65 V		2	2.7	Ω
				Full				3.1	
ON-state resistance matching between channels	Δr_{on}	V_{NO} or V_{NC} = 1.5 V, I_{COM} = –2 mA,	Switch ON, See Figure 13	25°C	1.65 V		0.16	0.3	Ω
				Full				0.3	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –2 mA,	Switch ON, See Figure 13	25°C	1.65 V		3		Ω
		V_{NO} or V_{NC} = 0.6 V, 1.5 V, I_{COM} = –2 mA,	Switch ON, See Figure 13	25°C			3	6	
				Full				8	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 0.3 V, V_{COM} = 1.65 V, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = 0.3 V,	Switch OFF, See Figure 14	25°C	1.95 V	–20	1.5	20	nA
				Full		–50		50	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 1.95 V, V_{COM} = 1.95 V to 0,	Switch OFF, See Figure 14	25°C	0 V	–1	0.1	1	µA
				Full		–10		10	
NC, NO ON leakage current	$I_{NC(ON)}$, $I_{NO(ON)}$	V_{NC} or V_{NO} = 0.3 V, V_{COM} = Open, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	1.95 V	–20	1.5	20	nA
				Full		–50		50	
COM OFF leakage current	$I_{COM(OFF)}$	V_{NC} or V_{NO} = 1.65 V, V_{COM} = 0.3 V, or V_{NC} or $V_{N\ O}$ = 0.3 V, V_{COM} = 1.65 V,	Switch OFF, See Figure 14	25°C	1.95 V	–20	1.5	20	nA
				Full		–50		50	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 1.95 V to 0, V_{COM} = 0 to 1.95 V,	Switch OFF, See Figure 14	25°C	0 V	–1	0.06	1	µA
				Full		–10		10	
COM ON leakage current	$I_{COM(ON)}$	V_{NC} or V_{NO} = Open, V_{COM} = 0.3 V, or V_{NC} or V_{NO} = Open, V_{COM} = 1.65 V,	Switch ON, See Figure 15	25°C	1.95 V	–20	1.5	20	nA
				Full		–50		50	
Digital Control Inputs (IN, $\overline{EN}$)(2)									
Input logic high	V_{IH}			Full		1.5		5.6	V
Input logic low	V_{IL}			Full		0		0.6	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	1.95 V	–100	25	100	nA
				Full		–100		100	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY (continued)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	4.5	45	61	ns
				Full	1.65 V to 1.95 V	4		63	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	5.4	12	19	ns
				Full	1.65 V to 1.95 V	5		21	
Break-before-make time	t_{BBM}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	5 V	4	31	60	ns
				Full	1.65 V to 1.95 V	3		65	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 22	25°C	1.8 V		4		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch OFF, See Figure 16	25°C	1.8 V		19		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND,	Switch ON, See Figure 16	25°C	1.8 V		57		pF
COM OFF capacitance	$C_{COM(OFF)}$	$V_{COM} = V_+$ or GND,	Switch ON, See Figure 16	25°C	1.8 V		36		pF
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND,	Switch ON, See Figure 16	25°C	1.8 V		57		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND,	See Figure 16	25°C	1.8 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 19	25°C	1.8 V		100		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 20	25°C	1.8 V		–64		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	Switch ON, See Figure 21	25°C	1.8 V		–64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 23	25°C	1.8 V		0.060		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	1.95 V		0.001	0.05	µA
				Full				0.1	

TYPICAL PERFORMANCE

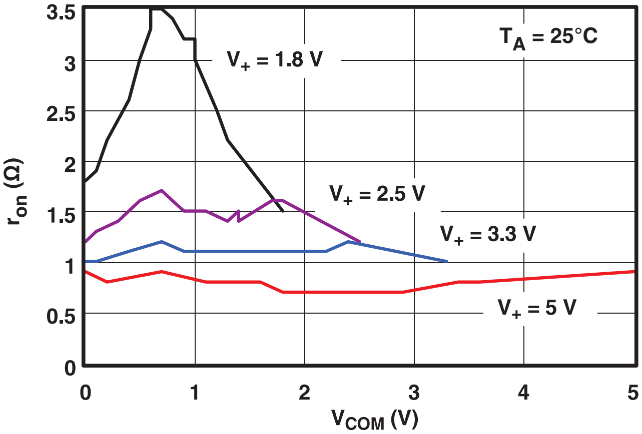


Figure 1. r_{on} vs V_{COM}

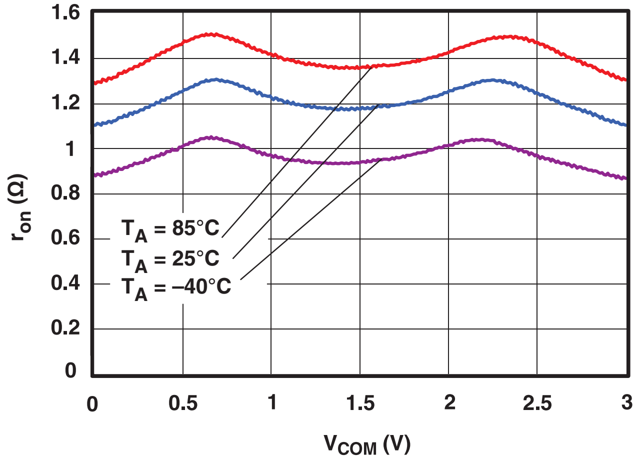


Figure 2. r_{on} vs V_{COM} (V_+ = 3 V)

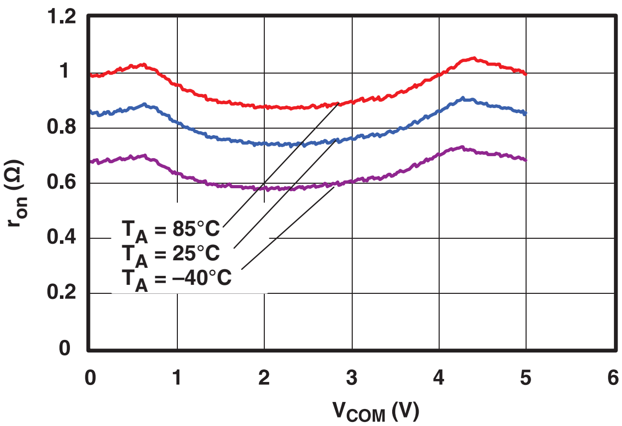


Figure 3. r_{on} vs V_{COM} (V_+ = 5 V)

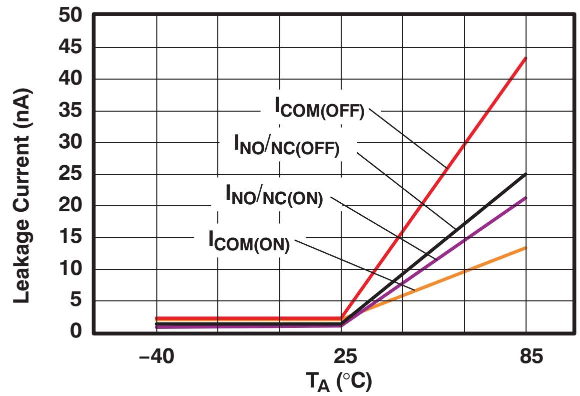


Figure 4. Leakage Current vs Temperature (V_+ = 5.5 V)

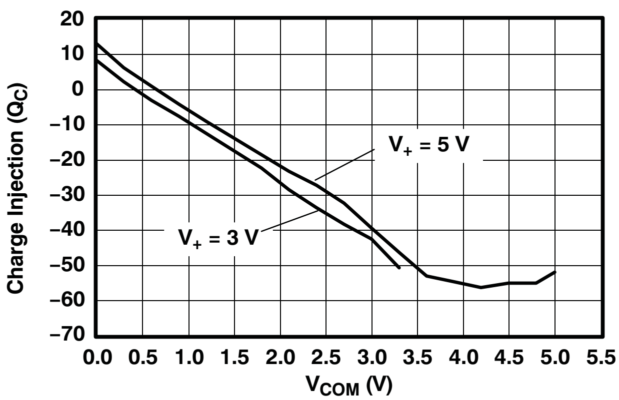


Figure 5. Charge Injection (Q_C) vs V_{COM}

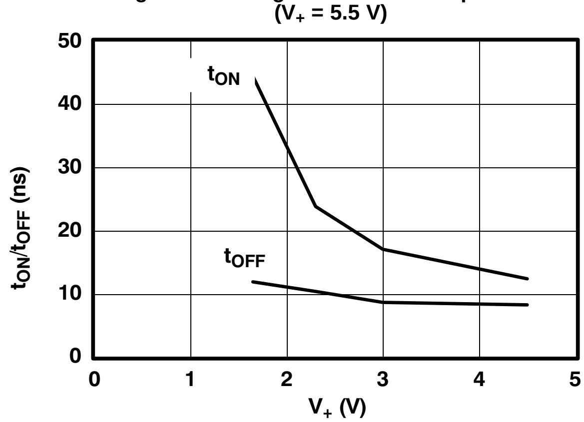


Figure 6. t_{ON} and t_{OFF} vs Supply Voltage

TYPICAL PERFORMANCE (continued)

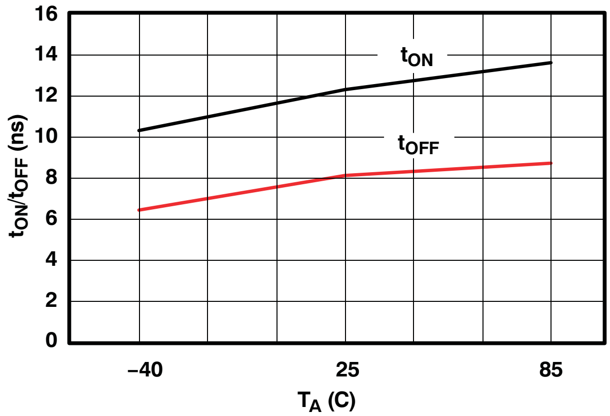


Figure 7. t_{ON} and t_{OFF} vs Temperature (V_+ = 5 V)

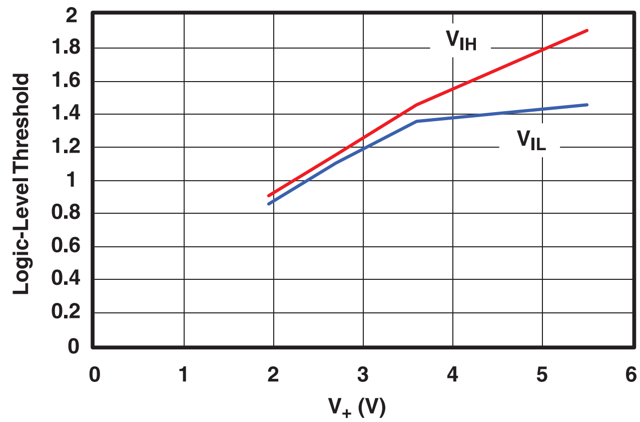


Figure 8. Logic-Level Threshold vs V_+

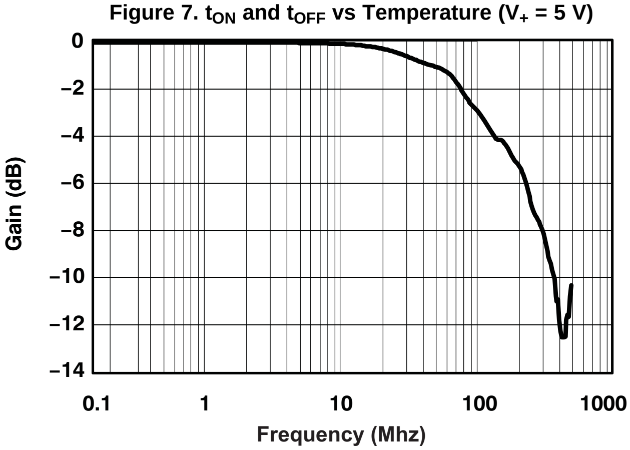


Figure 9. Bandwidth (V_+ = 5 V)

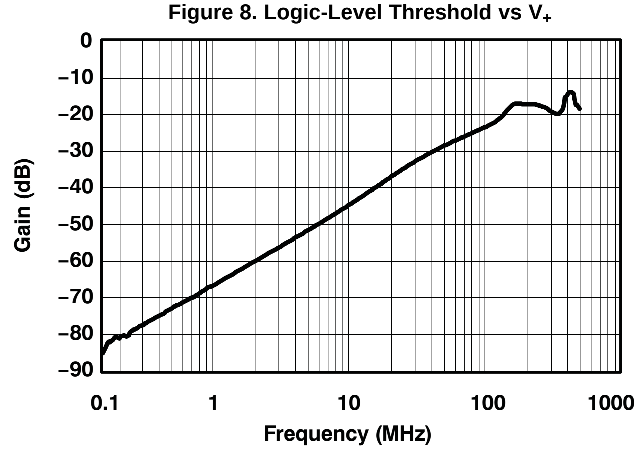


Figure 10. OFF Isolation and Crosstalk (V_+ = 5 V)

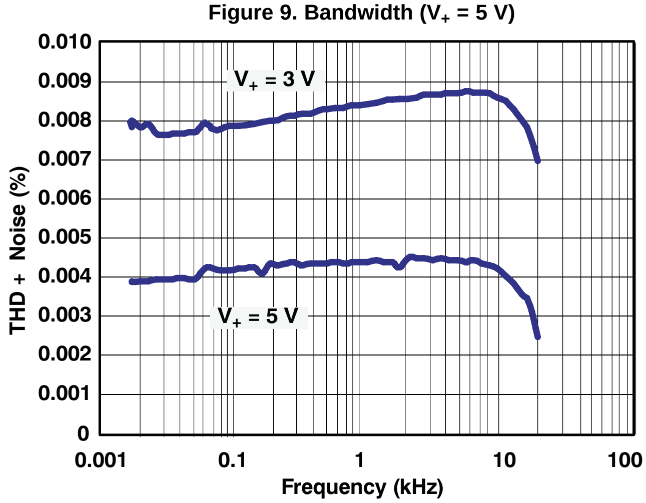


Figure 11. Total Harmonic Distortion (THD) vs Frequency

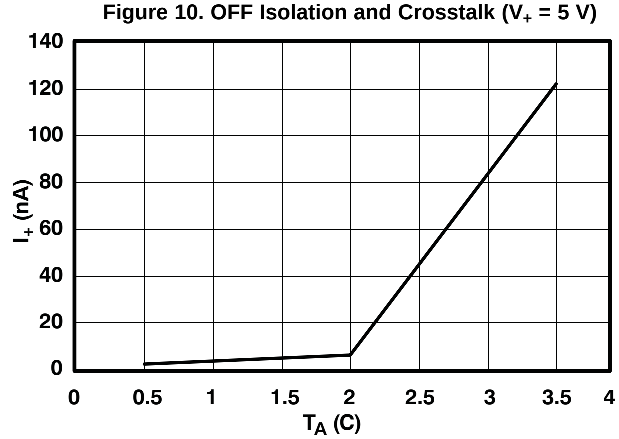


Figure 12. Power Supply Current vs Temperature (V_+ = 5 V)

PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	COM	Common
2	$\overline{EN}$	Enable control input
3	GND	Digital ground
4	GND	Digital ground
5	IN	Digital control to connect the COM to NO or NC
6	NO	Normally open
7	NC	Normally closed
8	V_+	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V_{COM}	Voltage at COM
V_{NC}	Voltage at NC
V_{NO}	Voltage at NO
r_{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
r_{peak}	Peak on-state resistance over a specified voltage range
Δr_{on}	Difference of r_{on} between channels in a specific device
$r_{on(flat)}$	Difference between the maximum and minimum value of r_{on} in a channel over the specified range of conditions
$I_{NC(OFF)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions
$I_{NC(PWROFF)}$	Leakage current measured at the NC port during the power-off condition, $V_+ = 0$
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
$I_{NO(PWROFF)}$	Leakage current measured at the NO port during the power-off condition, $V_+ = 0$
$I_{NC(ON)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open
$I_{COM(OFF)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the OFF state and the output (NC or NO) open
$I_{COM(PWROFF)}$	Leakage current measured at the COM port during the power-off condition, $V_+ = 0$
V_{IH}	Minimum input voltage for logic high for the control input (IN, $\overline{EN}$)
V_{IL}	Maximum input voltage for logic low for the control input (IN, $\overline{EN}$)
V_I	Voltage at the control input (IN, $\overline{EN}$)
I_{IH}, I_{IL}	Leakage current measured at the control input (IN, $\overline{EN}$)
t_{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF.
t_{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance, and ΔV_{COM} is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
$C_{NC(ON)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is ON

PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is OFF
C_I	Capacitance of control input (IN)
O_{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.
X_{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency where the gain of an ON channel is –3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of fundamental harmonic.
I_+	Static power-supply current with the control (IN, $\overline{EN}$) pin at V_+ or GND

PARAMETER MEASUREMENT INFORMATION

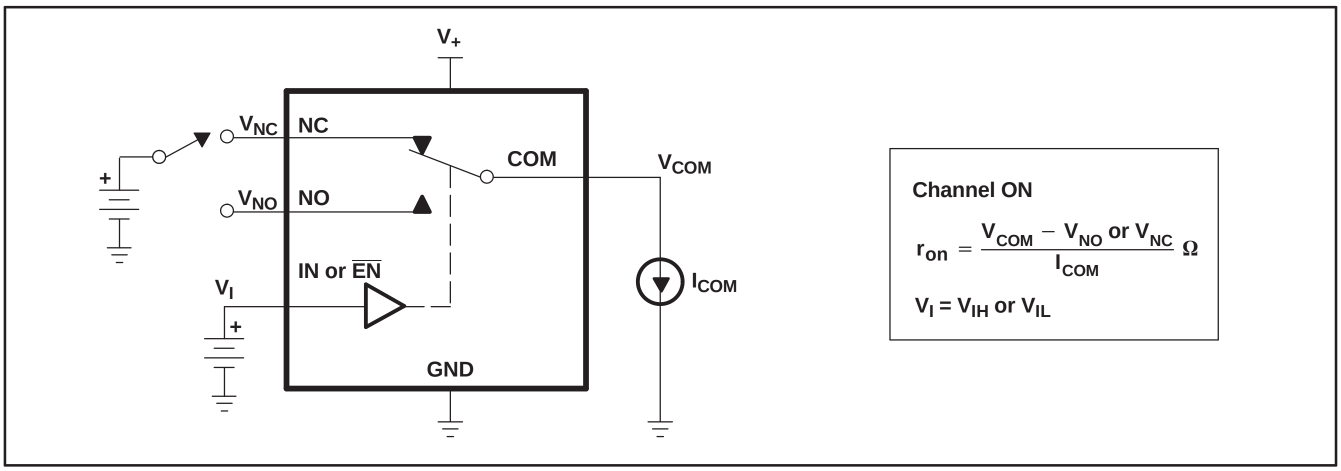


Figure 13. ON-State Resistance (r_{on})

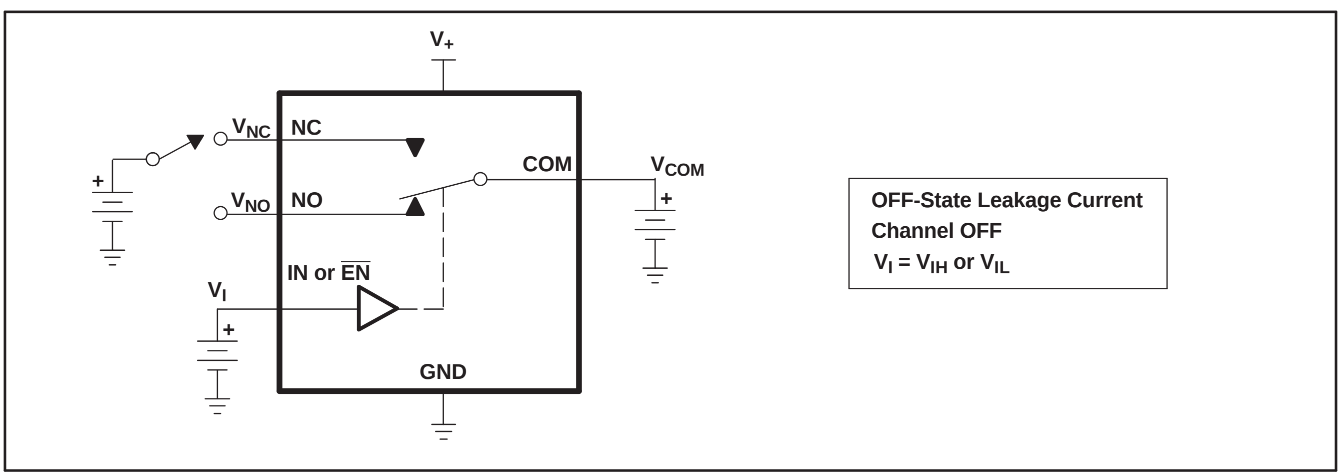


Figure 14. OFF-State Leakage Current ($I_{NC(OFF)}$, $I_{NO(OFF)}$, $I_{NO(PWROFF)}$, $I_{COM(PWROFF)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

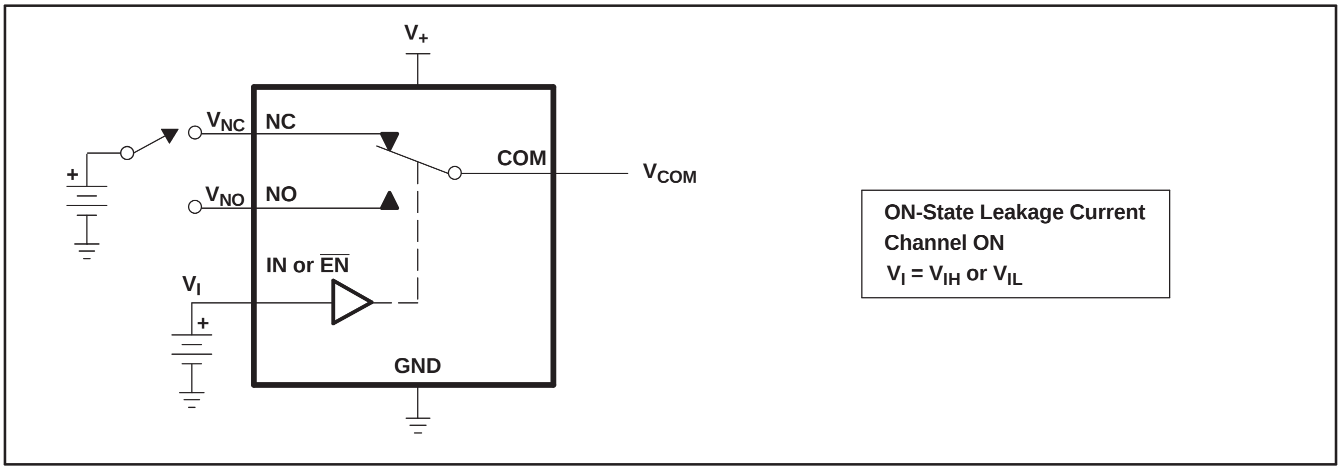


Figure 15. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)

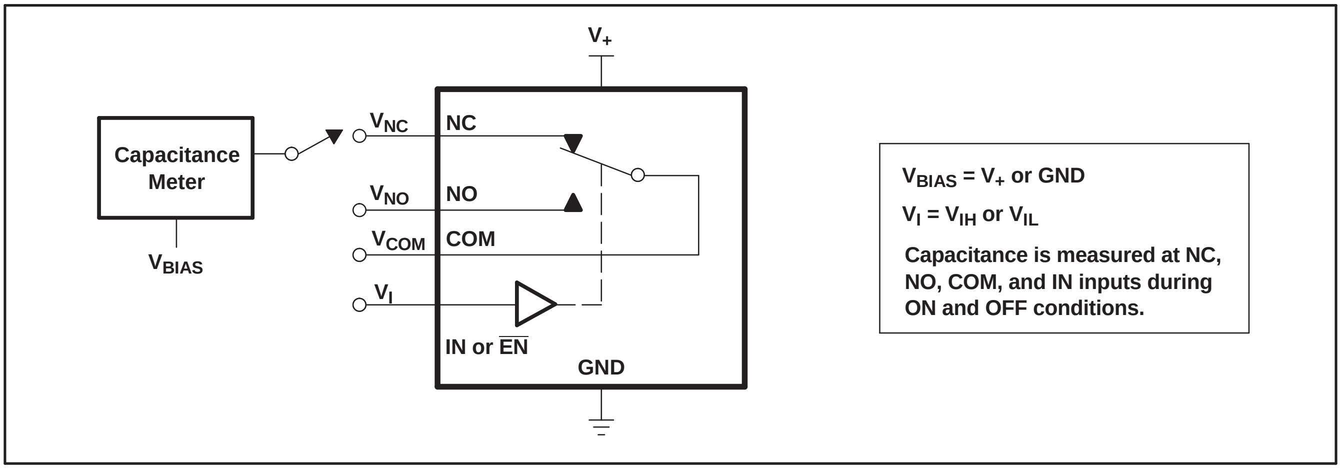
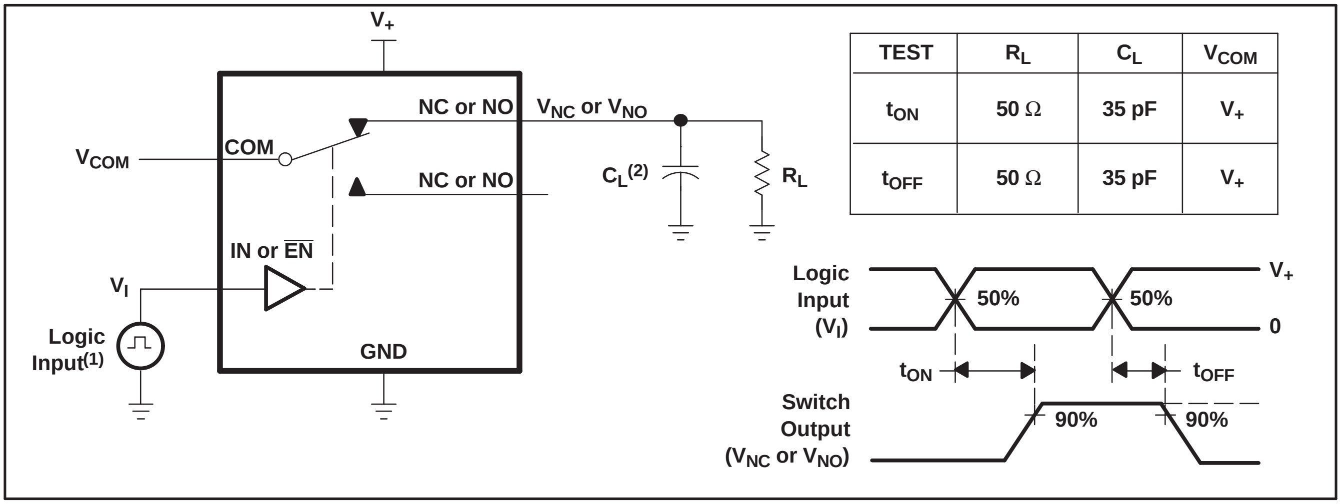


Figure 16. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NO(OFF)}$, $C_{NC(ON)}$, $C_{NO(ON)}$)

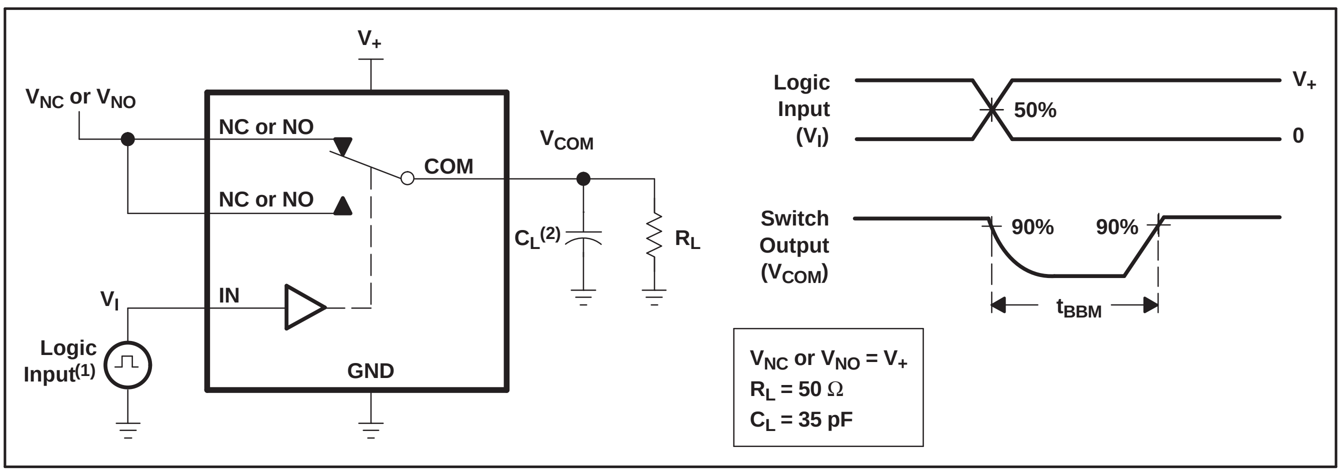
PARAMETER MEASUREMENT INFORMATION (continued)



TEST	R_L	C_L	V_{COM}
t_{ON}	50 Ω	35 pF	V_+
t_{OFF}	50 Ω	35 pF	V_+

(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 17. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 18. Make-Before-Break Time (t_{MBB})

PARAMETER MEASUREMENT INFORMATION (continued)

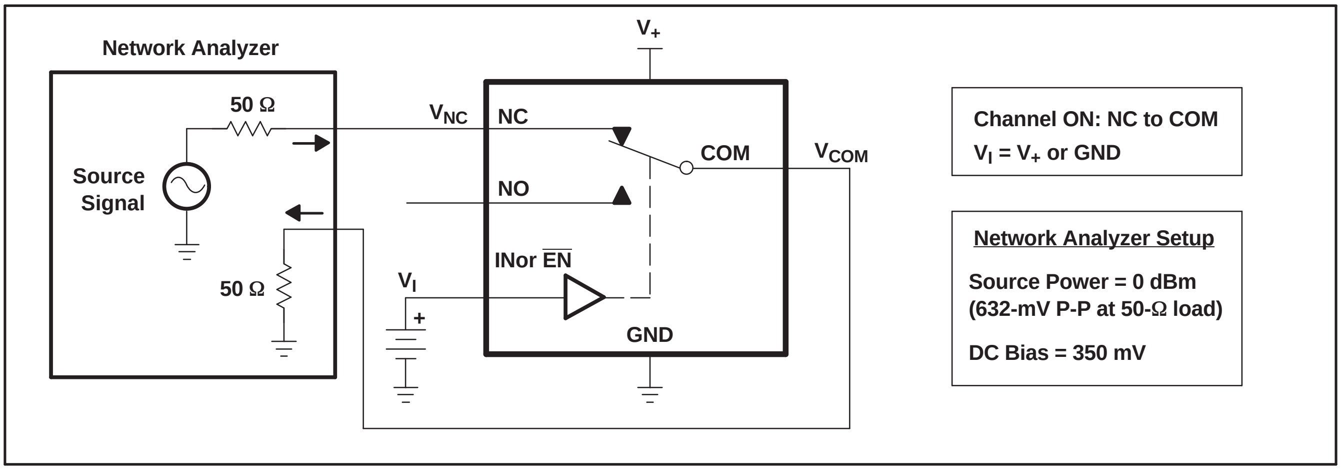


Figure 19. Bandwidth (BW)

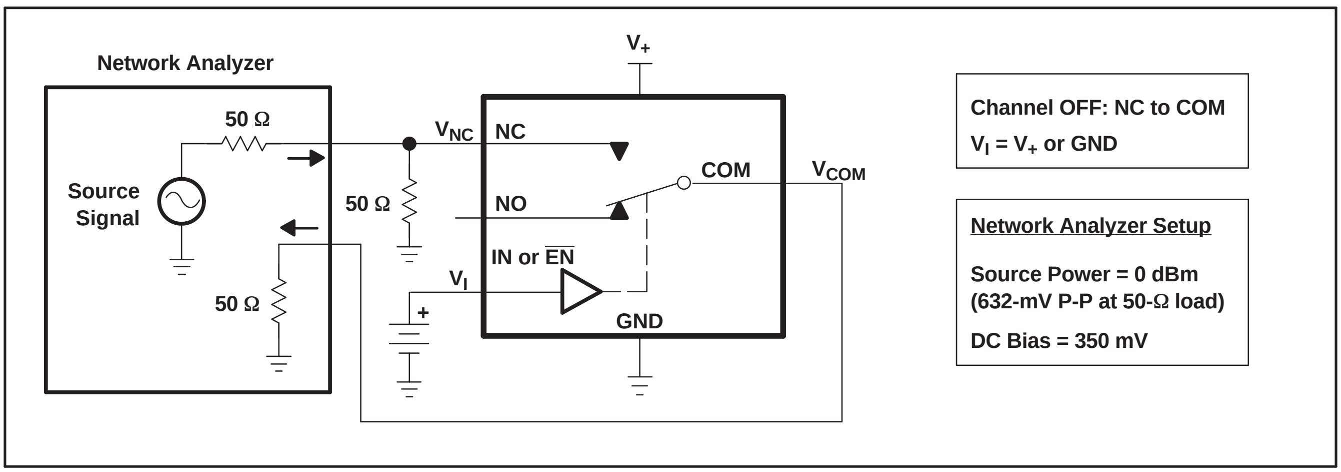


Figure 20. OFF Isolation (O_{ISO})

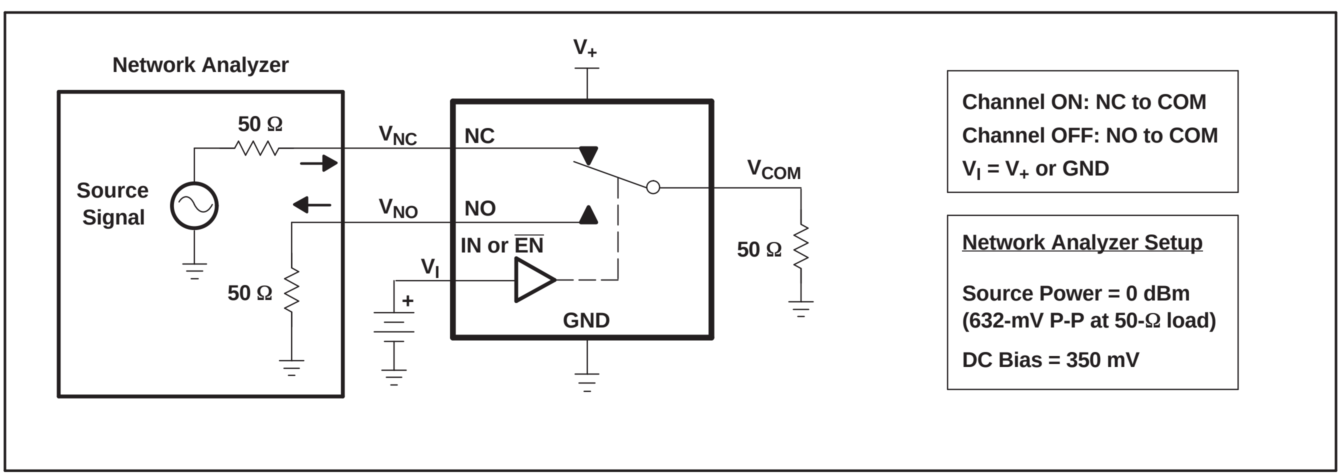
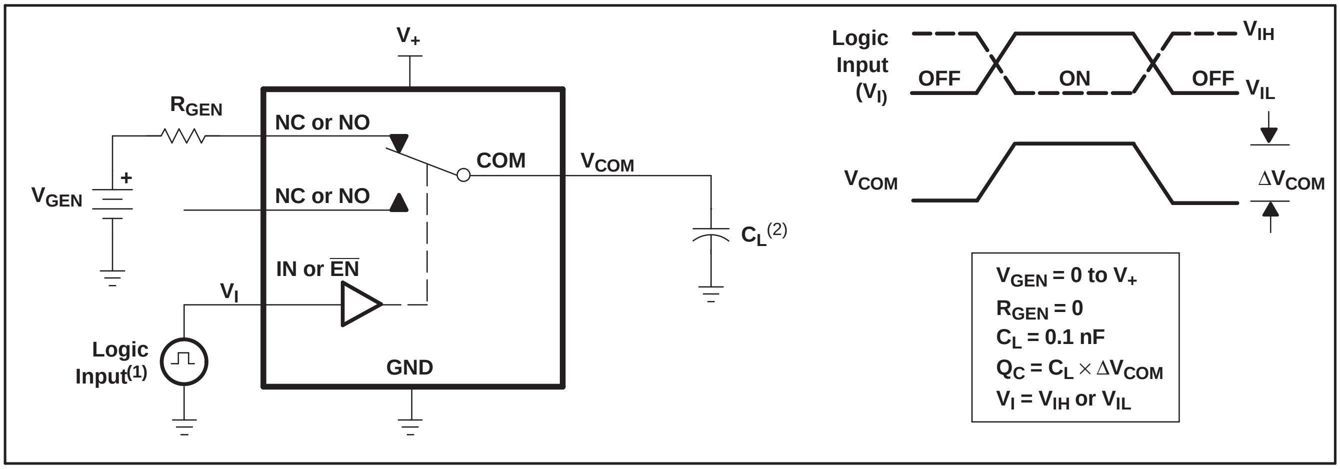


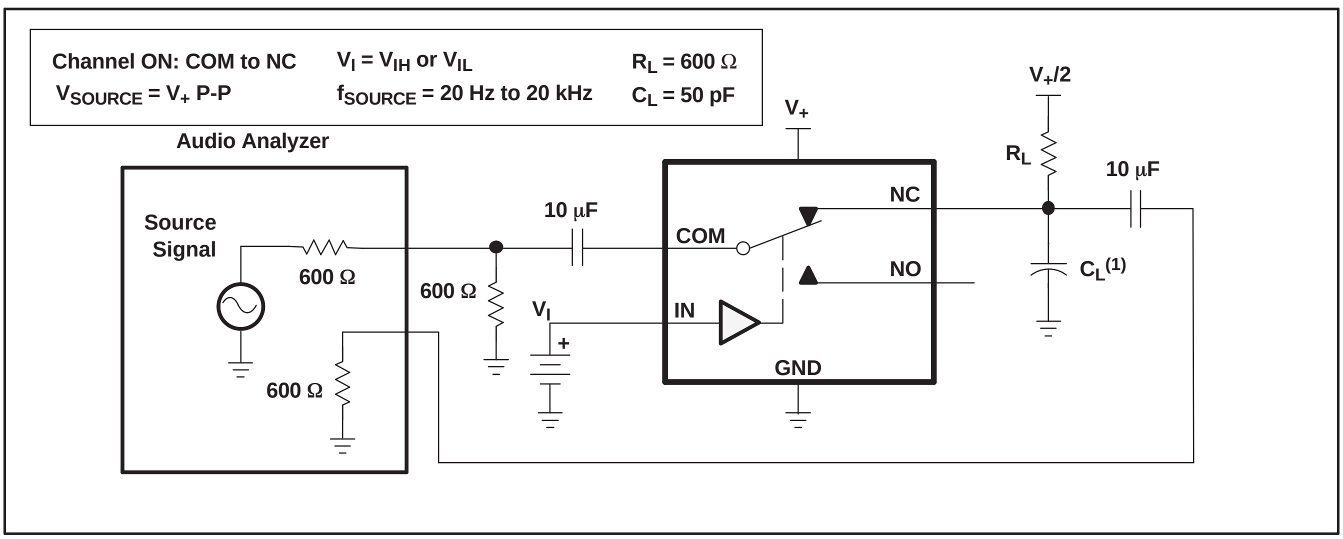
Figure 21. Crosstalk (X_{TALK})

PARAMETER MEASUREMENT INFORMATION (continued)



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 22. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 23. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A3153DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(JCDQ, JCDR)	Samples
TS5A3153YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	J5N	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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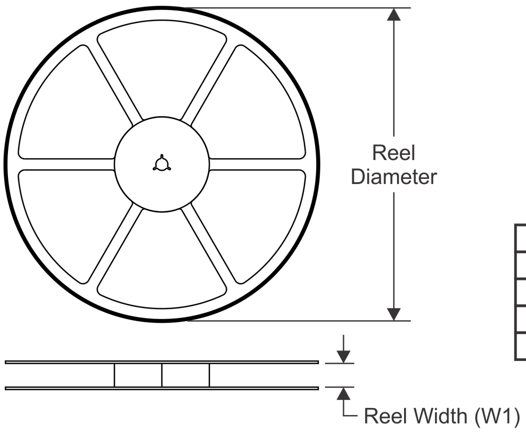
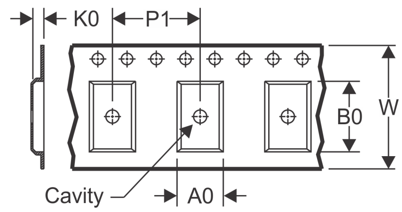
TAPE AND REEL INFORMATION

REEL DIMENSIONS

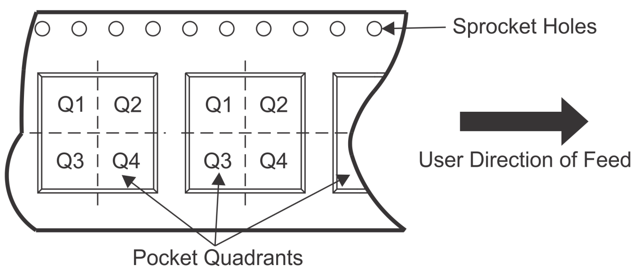


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

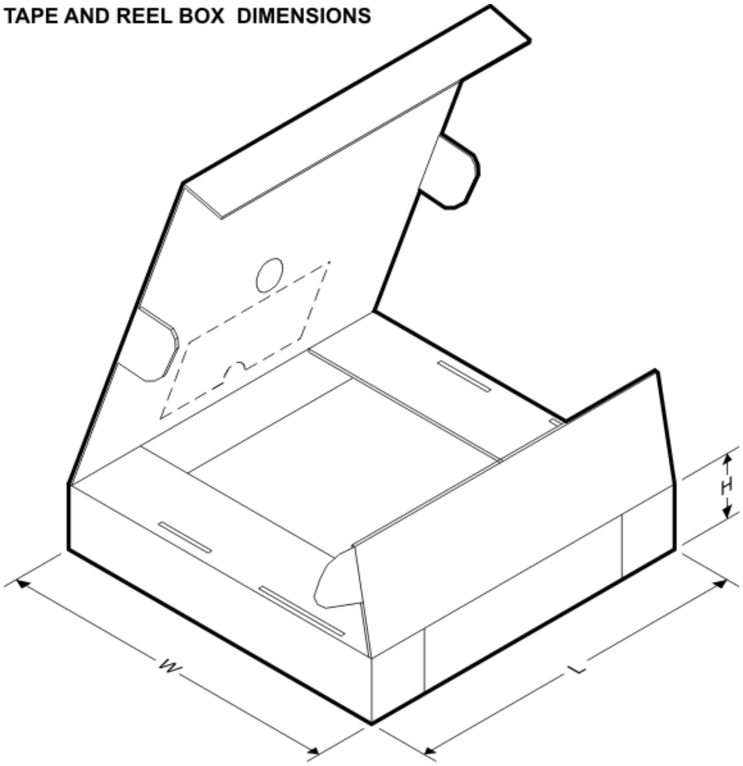
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A3153DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3153DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
TS5A3153YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

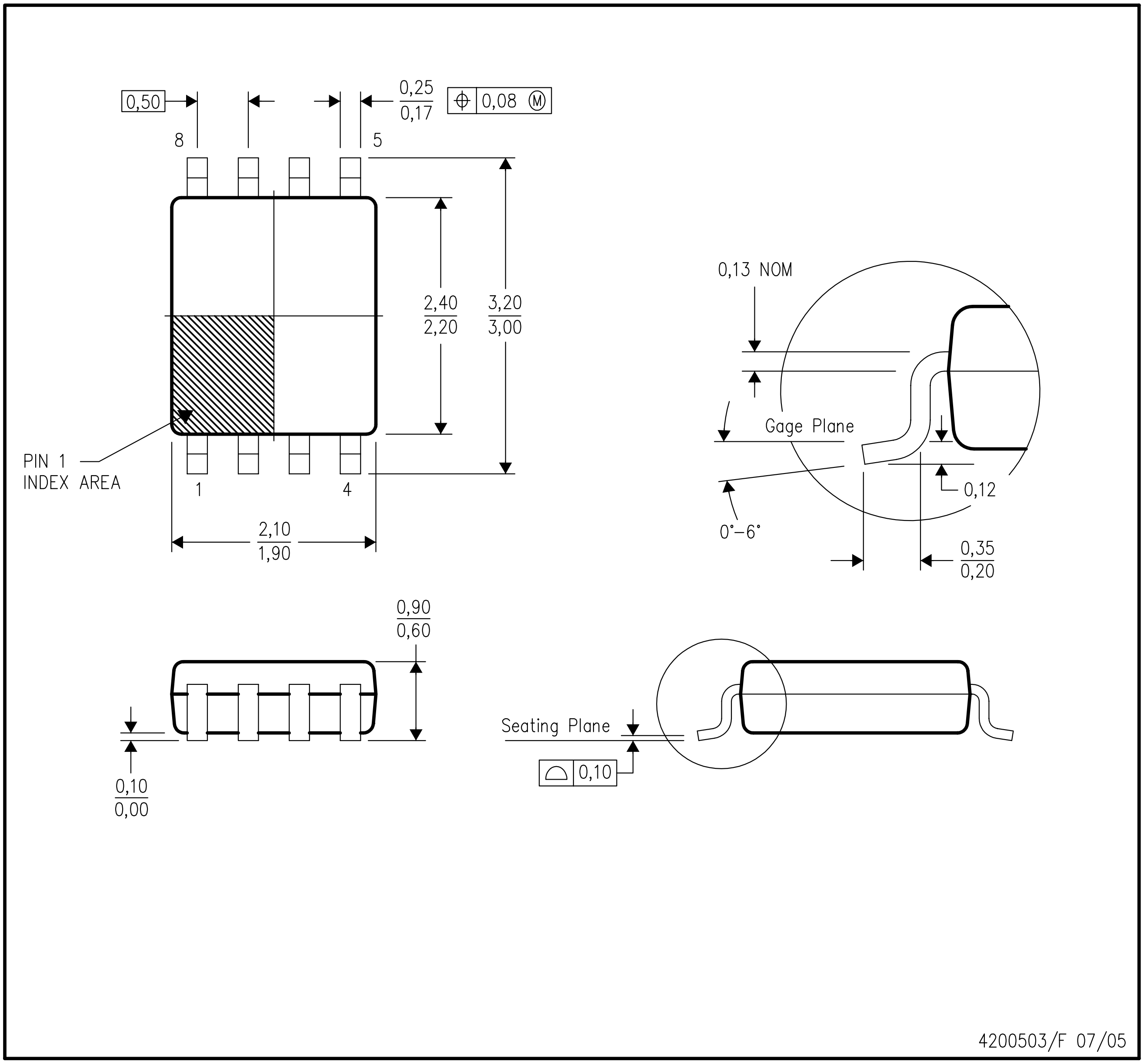
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

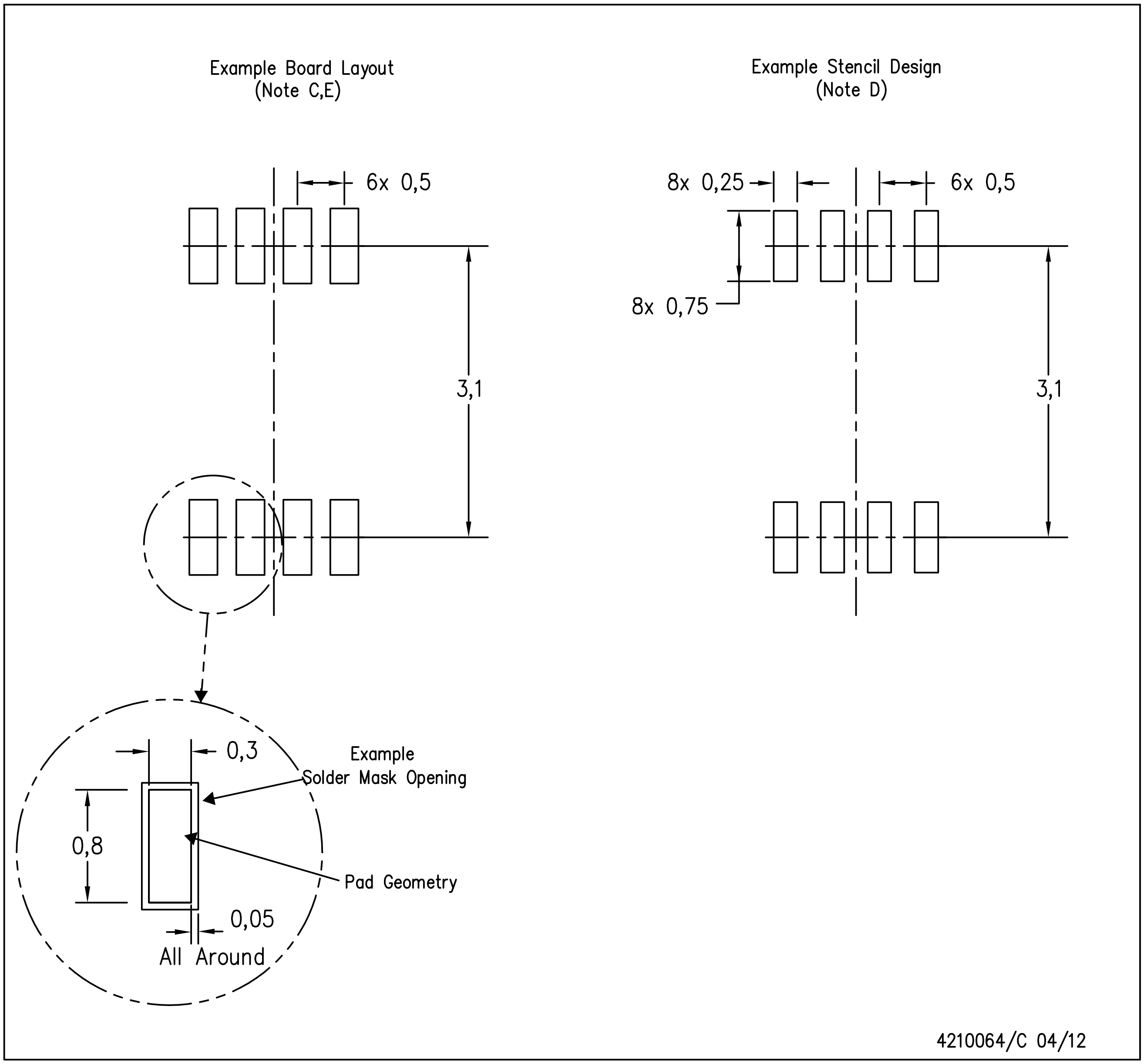
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A3153DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A3153DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A3153YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

DCU (R-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)

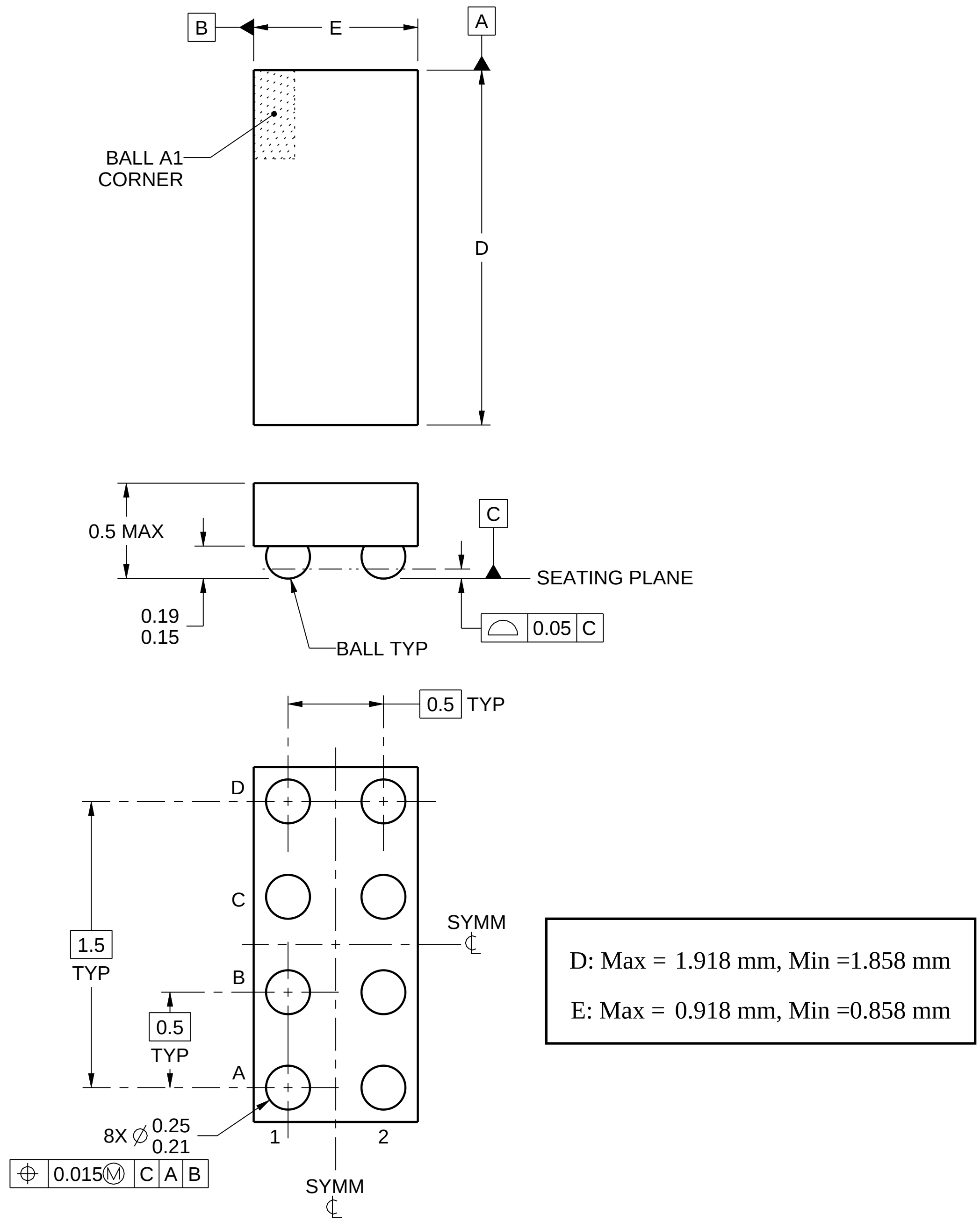


NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO-187 variation CA.

DCU (S-PDSO-G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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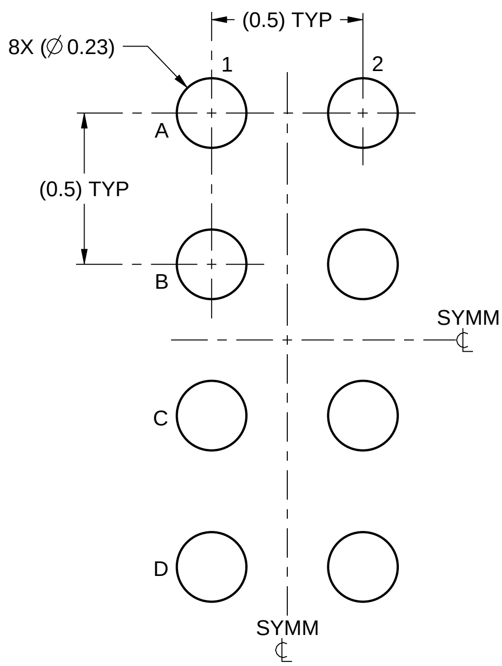
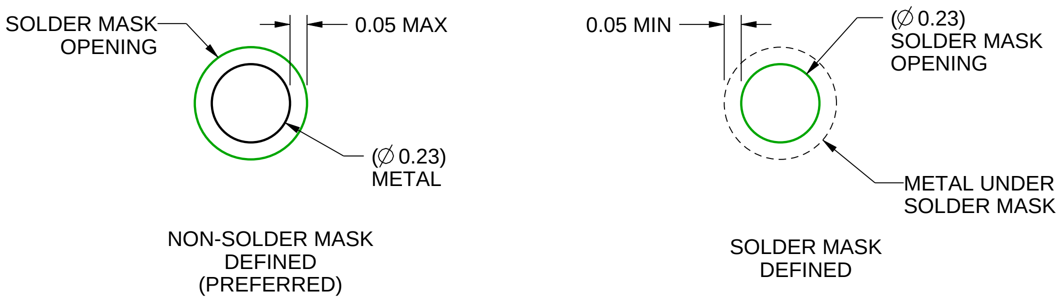
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

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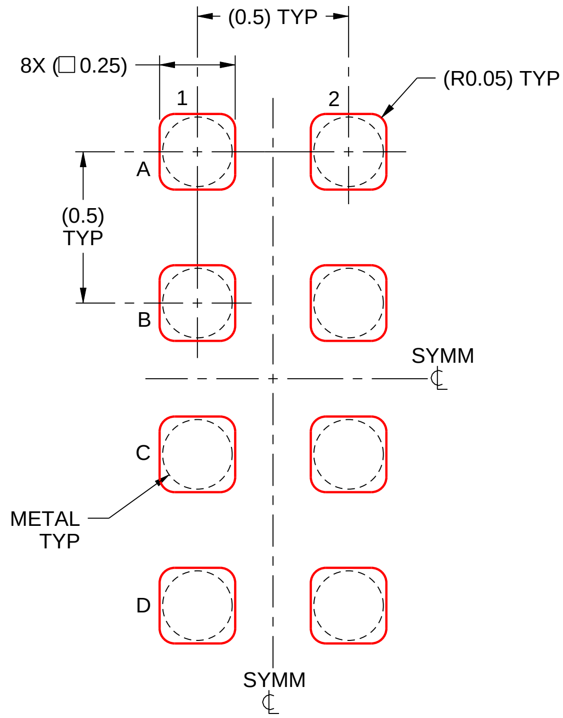
NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.